

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1533		SERIAL NO. 09/754,926	
<div>DIPE JC164 AUG 06 2001 PATENT & TRADEMARK OFFICE</div> <p>LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</p>				APPLICANT Micron Technology, Inc.			
				FILING DATE January 4, 2001		GROUP 2812	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA							
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
AB							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EK	AC		"Tunneling Leakage Current In Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics", Ying Shi, Xiewen Wang, and T.P. Ma; pp. 388-390; IEEE Electron Device Letters; Vol. 19, No. 10, October 1998				
EK	AD		"High Quality Ultra-thin (1.5 nm) TiO ₂ /Si ₃ N ₄ Gate Dielectric for Deep Sub-micron CMOS Technology", Xin Guo, Xiewen Wang, Zhijiong Luo, T.P. Ma, and T. Tamagawa; 1999 IEEE; IEDM; pp. 137-140				
	AE		"High Quality Ta₂O₅ Gate Dielectrics with T_{ox,eq}<10Å"; H.F. Luan, S.J. Lee, C.H. Lee, S.C. Song, Y.L. Mao, Y. Senzaki, D. Roberts, and D.L. Kwong; IEDM; pp. 141-144				
EK	AF		"A Novel High K Inter-Poly Dielectric(IPD), Al ₂ O ₃ for Low Voltage/High Speed Flash Memories; Erasing in msccs at 3.3V; W.H. Lee, J.T. Clemens, R.C. Keller, and L. Manchanda; 1997 Symposium on VLSI Technology Digest of Technical Papers; pp. 117-118				
EK	AG		"Substrate dependence on the optical properties of Al ₂ O ₃ films grown by atomic layer deposition"; Y. Kim, S.M. Lee, C.S. Park, S.I. Lee, and M.Y. Lee; Appl. Phys. Lett. 71 (25) 22 December 1997; pps 3604-3606				
EK	AH		"The effects of oxidation temperature on the capacitance-voltage characteristics of Oxidized AlN films on Si"; J. Kolodzey, E.A. Chowdhury, G. Qui, J. Olowolafe, C.P. Swann; K.M. Unruh; J. Suehle, R.G. Wilson, J.M. Zavada; Appl. Phys. Lett. 71 (26) 29 December 1997; pp. 3802-3804				
EK	AI		"High K Dielectrics for CMOS and Flash"; L. Manchanda; Extended Abstracts of the 1999 Internatioanl Conference on Solid State Devices and Materials, Tokyo; pp. 150-151				
	AJ		Article: "High-K Dielectrics for Giga-Scale CMOS and Non-Volatile Memory Technology"; L. Manchanda, G. Aiers, and J.P. Han				
EXAMINER <i>Eric K. Kohn</i>				DATE CONSIDERED 2/20/01			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AC	Article: "Application of Al ₂ O ₃ Grown by Atomic Layer Deposition to DRAM and FeRAM; C.T. Kim, C. Lim, K.M. Kim, M.S. Kim, H.K. Jang, Y.S. Yu and J.S. Roh					
EK	AD	"Aluminum oxide films obtained by electron-beam evaporation"; L.V. Veidenbakh and S. N. Gromova; Sov. J. Opt. Technology. 50 (9) Sept. 1983; © 1984 The Optical Society of America; pp. 566-568					
EK	AE	"Investigation of aluminum oxide films by mass- and IR-spectrometric methods"; S.N. Gromova, E.A. Nikolaeva, and E.V. Prokof'ev; Sov. J. Opt. Technol. 56(11), Nov. 1989; © 1990 The Optical Society of America; pp. 667-669					
EK	AF	"Effect of substrate temperature on density of aluminum oxide films" E.B. Briki; Sov. J. Opt. Technol. 57(1), Jan 1990; © 1990 The Optical Society of America; pp. 50-52					
	AG	Article: Beam Solid Interactions: Fundamentals and Applications; Materials Research Society Symposium Proceedings; Volume 279; pp. 825-830					
	AH	"Effect of Plasma Activation on the Phase Transformations of Aluminum Oxide"; O. Zywitzki, G. Hoetzel; Surface & Coatings Technology; pp. 754-762					
	AI	Article: "Tunability of Intrinsic Stress in SiO ₂ Dielectric Films Formed By Molecular Beam Deposition"; Naresh Chand, R.R. Kola, J.W. Osenbach, and W.T. Teang"; pp. 195-200					
EK	AJ	"Rapid thermal oxidation of silicon monoxide"; E. Fogarassy, A. Slaoui, C. Fuchs, and J.L. Regolini; Appl. Phys. Lett. 51(5), 3 August 1987; © 1987 American Institute of Physics; pp. 337-339					
EXAMINER <i>Era Kula</i>				DATE CONSIDERED <i>2/20/02</i>			
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EK	AD	"Low Temperature Ion-Assisted Deposition of Thermally Evaporated Silicon Monoxide"; I.C. Stevenson; Society of Vacuum Coaters; 37 th Annual Technical Conference Proceedings (1994); pp. 81-84					
	AE	"Optical Thin Films IV: New Developments"; James D. Rancourt; SPIE - The International Society for Optical Engineering; Volume 2262; pp. 14-21					
EK	AF	Article from IBM Website, Intellectual Property Network; US 5923056: "Electronic components with doped metal oxide dielectric materials and a process for making electronic components with doped metal oxide dielectric material"; Lee; Woo-Hyeong and Manchanda; Lalita; issued 7/13/99					
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EXAMINER <i>E. H. Kim</i>				DATE CONSIDERED <i>2/20/02</i>			
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